

SSCP3906GS7

PNP Switching Transistor

Features

VCB	VCE	VBE	VCESAT	IC
-40V	-40V	-5V	-400mV	-200mA

Description

The PNP Transistor is designed for use in linear and switching applications. The device is housed in the SOT-323 package, which is designed for telephony and professional communication equipment.

Applications

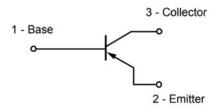
- General purpose switching and amplification
- Telephony and professional communication equipment

Ordering Information

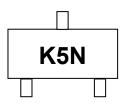
Device	Package	Shipping	
SSCP3906GS7	SOT-323	3000/Reel	

> Pin configuration





Circuit Diagram



Marking(Top View)



ightarrow Absolute Maximum Ratings(T_A=25°C unless otherwise noted)

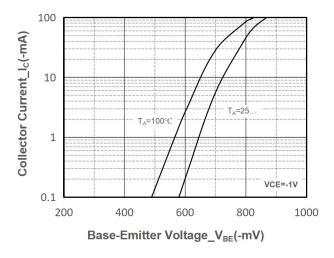
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector- Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current-Continuous	Ic	-200	mA
Collector Power Dissipation	Pc	200	mW
Junction Temperature	TJ	150	$^{\circ}$
Storage Temperature	T _{STG}	-55 to 150	$^{\circ}$

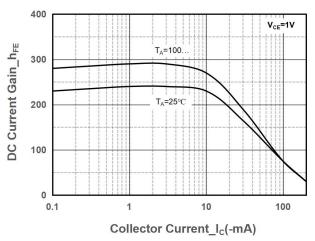
➤ Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-10uA,I _E =0	-40			V
Collector-emitter Breakdown Voltage	BV _{CEO}	I _C =-1mA,I _B =0	-40			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E =-10uA,I _C =0	-5			V
Collector Cutoff Current	I _{CEX}	V _{CE} =-30V, V _{EB} =-3V			-50	nA
Collector Cutoff Current	I _{CBO}	V _{CB} =-30V,I _E =0			-100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =-3V,I _C =0			-100	nA
		V _{CE} =-1V,I _C =-10mA	100		300	
DC Current Gain	h _{FE}	V _{CE} =-1V,I _C =-0.1mA	60			
		V _{CE} =-1V,I _C =-100mA	30			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I_C =-50mA, I_B =-5mA			-0.4	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-50mA,I _B =-5mA			-0.95	V
Transition frequency	f⊤	V _{CE} =-20V,I _C =-10mA f=100MHz	250			MHz
Delay Time	t _d	V _{CC} =-3V,V _{BE} =0.5V			35	ns
Rise Time	t _r	I _C =-10mA,I _{B1} =-1mA			35	ns
Storage Time	ts	V _{CC} =-3V,I _C =-10mA			225	ns
Fall Time	t _f	I _{B1} =-I _{B2} =-1mA			75	ns



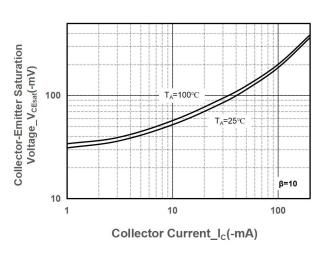
\succ Typical Performance Characteristics (T_A=25°C unless otherwise noted)



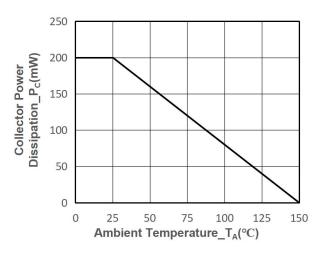


Collector Current vs. Base-Emitter Voltage

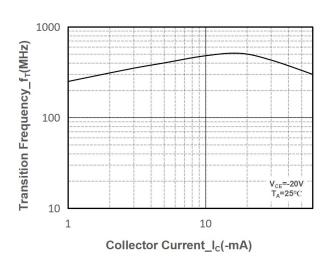
DC Current Gain vs. Collector Current



V_{BE(sat)} vs. Collector Current



V_{CE(sat)} vs. Collector Current

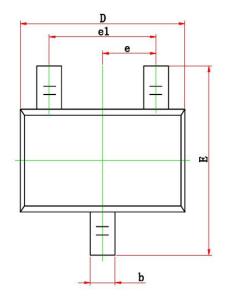


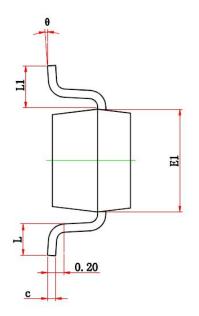
Power derating vs. Ambient temperature

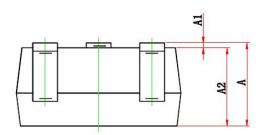
Transition Frequency vs. Collector Current



Package Information







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	2.150	2.450	0.085	0.096	
E1	1.150	1.350	0.045	0.053	
е	0.650 TYP.		0.026	TYP.	
e1	1.200	1.400	0.047	0.055	
L	0.260	0.460	0.010	0.018	
L1	0.525 REF.		0.021 REF.		
θ	0°	8°	0°	8°	



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